

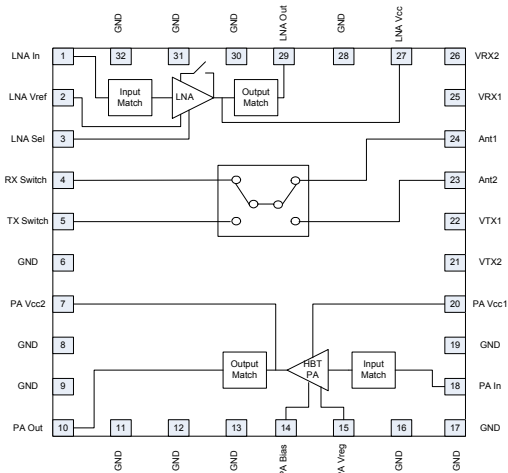


Features

- Integrated LNA, PA, and Transfer Switch
- Small Form Factor 8.0mm x 8.0mm x 1.2mm
- 50Ω Inputs and Outputs
- Low Insertion Loss, High Isolation Transfer Switch
- 33.5dBm PA Output Power
- Low PA Harmonic Content

Applications

- 868MHz/900MHz ISM Band Application
- Single Chip RF Front End Module
- Portable Battery Powered Equipment
- Wireless Automatic Metering Applications



Functional Block Diagram

Product Description

The RFFM6904 is a single-chip front-end module (FEM) for applications in the 868MHz/900MHz ISM Band. The RFFM6904 addresses the need for aggressive size reduction for typical portable equipment RF front-end design and greatly reduces the number of components outside of the core chipset thus minimizing the footprint and assembly cost of the overall solution. The RFFM6904 contains an integrated 2 Watt PA, TX/RX transfer switch, LNA with bypass mode, and matching components. The RFFM6904 is packaged in a 32-pin, 8.0mm x 8.0mm x 1.2mm over-molded laminate package with backside ground which greatly minimizes next level board space and allows for simplified integration.

Optimum Technology Matching® Applied

- | | | | |
|--|--------------------------------------|--|------------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input type="checkbox"/> BIFET HBT |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

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Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--------------------------------|-------------|------|
| Overall | | |
| DC Supply Voltage | +5.0 | V |
| Operating Ambient Temperature | -40 to +85 | °C |
| Storage Temperature | -40 to +150 | °C |
| Low Noise Amplifier | | |
| DC Supply Current | 32 | mA |
| Input RF Power | 5 | dBm |
| Power Amplifier | | |
| DC Supply Current | 1200 | mA |
| Input RF Power | 10 | dBm |
| Transmit/Receive Switch | | |
| Input RF Power | 33 | dBm |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2002/95/EC.

| Parameter | Specification | | | Unit | Condition |
|---|---------------|------------|-------|------|--|
| | Min. | Typ. | Max. | | |
| Low Noise Amplifier | | | | | |
| Frequency Range | 868 | 902 to 928 | | MHz | |
| High Gain Mode | | | | | |
| Gain | 17 | 21 | 23.5 | dB | Gain Select < 0.8V Over LNA V _{CC} , LNA V _{REF} , Temperature, and Frequency |
| Noise Figure | | 1.3 | 1.5 | dB | LNA V _{REF} = LNA V _{CC} = 3.3V |
| Input IP3 | -4.5 | -1 | | dBm | T _{AMB} = +25°C, LNA V _{CC} = 3.3V |
| Input Gain Compression | -15 | | | dBm | |
| Input Return Loss | | -8 | -5 | dB | |
| Output Return Loss | | -8 | -6 | dB | |
| LNA Operating Current | | | 15 | mA | LNA V _{REF} = LNA V _{CC} = 3.3V |
| LNA Enable | | | 1 | mA | |
| Stability, Input VSWR | 10:1 | | | | All phase angles |
| Output Spurious | | | -70 | dBc | |
| Low Gain Mode | | | | | |
| Gain | -7 | -6 | | dB | |
| Input IP3 | 15.5 | 17 | | dBm | T _{AMB} = +25°C, LNA V _{CC} = 3.3V |
| Current Drain | | 1.5 | 3 | mA | |
| Power Amplifier | | | | | |
| Frequency Range | 868 | 902 to 928 | | MHz | |
| PA V _{CC1} = PA V _{CC2} = PA BIAS | 3.2 | 4.0 | 4.5 | V | |
| PA V _{REG} | 2.75 | 2.85 | 2.95 | V | |
| P _{OUT} | 32.5 | 33.5 | | dBm | Saturated power output |
| Gain | 27 | 30 | | dB | PA V _{CC1} = PA V _{CC2} = PA BIAS = 4V, over temperature and frequency |
| Output Harmonic Levels | | | | | |
| 2nd | | | -42.5 | dBc | |
| 3rd through 10th | | | -72.5 | dBc | PA V _{CC1} = PA V _{CC2} = PA BIAS = 4V, over temperature and frequency |

| Parameter | Specification | | | Unit | Condition |
|--------------------------------|---------------|------------|------|---------|---|
| | Min. | Typ. | Max. | | |
| Power Amplifier, cont. | | | | | |
| Efficiency | 40 | | | % | 33.5dBm output, PA V_{CC1} = PA V_{CC2} = PA BIAS = 4.0V, 2.85V V_{REG} |
| Input Return Loss | 9 | | | dB | |
| Output Spurious | | | -70 | dBc | |
| Stability | | 10:1 | | | All phase angles |
| | | 7:1 | | | All phase angles, -40 °C |
| Current | | | | | |
| Operating | | 750 | 1000 | mA | 33.5dBm output, PA V_{CC1} = PA V_{CC2} = PA BIAS = 4.0V, 2.85V V_{REG} |
| Bias Only | | | 200 | mA | Idle current, no RF at input |
| I_{REG} | | 2 | 6 | mA | |
| Leakage Current | | 0.1 | 0.9 | μ A | Over V_{CC} , Frequency, and Temperature |
| Transmit/Receive Switch | | | | | |
| Frequency Range | 868 | 902 to 928 | | MHz | |
| Insertion Loss | | | | | |
| TX to ANT1 or ANT2 | | 0.85 | 1.4 | dB | |
| RX to ANT1 or ANT2 | | 0.95 | 1.4 | dB | |
| Any Path (1800MHz to 1860MHz) | 2 | | | dB | |
| Any Path (2700MHz to 2790MHz) | 2 | | | dB | |
| Any Path (>3600MHz) | 15 | | | dB | |
| Isolation (All Paths) | 18 | | | dB | |
| Input IP3 | 55 | | | dBm | |
| Thermal Resistance | | 47.8 | | °C/W | 4V V_{CC} , 2.85V V_{REG} , 31dBm P_{OUT} , T_{REF} = 85 °C |
| Output Harmonic Levels | | | | | |
| 2nd | | | -60 | dBc | |
| 3rd through 10th | | | -80 | dBc | |
| Input 1dB Gain Compression | 30 | 32 | | dBm | |
| Return Loss (All Ports) | 18 | | | dB | Active ports only |
| Switch Control Logic HIGH | 2.6 | | 3.5 | V | |
| Switch Control Logic LOW | 0 | | 0.2 | V | |
| Switch Control Current | | | 5 | μ A | VTX2, VRX1, and VRX2 |
| | | | 40 | μ A | VTX1 |
| Transition Time | | | 2 | μ A | Settle to 0.25dB of final value |

| Connected Path | RX SW to ANT1 | RX SW to ANT2 | TX SW to ANT1 | TX SW to ANT2 |
|----------------|---------------|---------------|---------------|---------------|
| VRX1 | High | Low | Low | Low |
| VRX2 | Low | High | Low | Low |
| VTX1 | Low | Low | High | Low |
| VTX2 | Low | Low | Low | High |

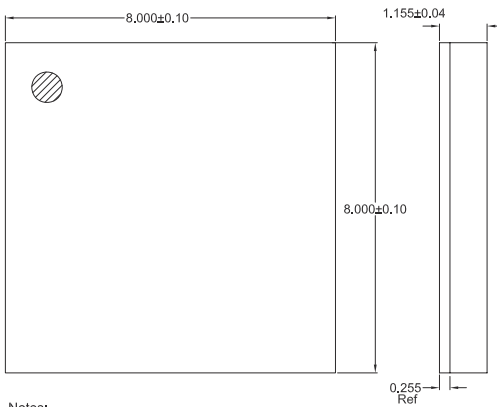
*Switch Control Logic High = Min 2.6V to Max 3.5V

*Switch Control Logic Low = Min 0.0V to Max 0.2V

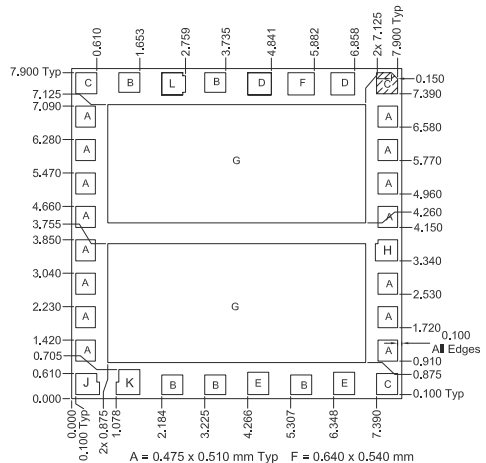
Pin Names and Description

| Pin | Name | Description |
|----------|-----------------|---|
| 1 | LNA IN | RF Input to the low noise amplifier, 50Ω nominal impedance. |
| 2 | LNA VREF | Voltage to set the bias level to the LNA, 3.0V nominal, can be used to shut the LNA off or to adjust the quiescent current. |
| 3 | LNA SELECT | A logic low selects the high gain mode of the LNA, logic high selects the low gain mode. |
| 4 | RX SWITCH INPUT | RF port from the Switch going to the LNA input, 50Ω nominal impedance. |
| 5 | TX SWITCH INPUT | RF port from the Switch going to the PA output, 50Ω nominal impedance. |
| 6 | GND | Ground. |
| 7 | PA VCC2 | Voltage supply for the Power Amplifier, nominal voltage is 3.6V. |
| 8 | GND | Ground. |
| 9 | GND | Ground. |
| 10 | PA OUT | RF output from the Power Amplifier, 50Ω nominal impedance and DC blocked. |
| 11 | GND | Ground. |
| 12 | GND | Ground. |
| 13 | GND | Ground. |
| 14 | PA BIAS | Voltage supply for the Power Amplifier bias network, nominal voltage is 3.6V. |
| 15 | PA VREG | Voltage to set the bias level of the Power Amplifier, nominal voltage is 2.85V. |
| 16 | GND | Ground. |
| 17 | GND | Ground. |
| 18 | PA IN | RF Input to the Power Amplifier, 50Ω nominal impedance. |
| 19 | GND | Ground. |
| 20 | PA VCC1 | Voltage supply for the Power Amplifier, nominal voltage is 3.6V. |
| 21 | VTX2 | Logic input to the Switch, see Logic Table below. |
| 22 | VTX1 | Logic input to the Switch, see Logic Table below. |
| 23 | ANT2 | RF port from the Switch going to Antenna 1, 50Ω nominal impedance. |
| 24 | ANT1 | RF port from the Switch going to Antenna 2, 50Ω nominal impedance. |
| 25 | VRX1 | Logic input to the Switch, see Logic Table below. |
| 26 | VRX2 | Logic input to the Switch, see Logic Table below. |
| 27 | LNA VCC | LNA Collector Voltage, nominal voltage is 3.0V. |
| 28 | GND | Ground. |
| 29 | LNA OUT | RF Output from the low noise amplifier, 50Ω nominal impedance and DC blocked. |
| 30 | GND | Ground. |
| 31 | GND | Ground. |
| 32 | GND | Ground. |
| Pkg Base | GND | The central metal base of package provides DC and RF GND as well as heat sink for the amplifier. |

Package Drawing



Notes:
1. Shaded area represents Pin 1 location



- A = 0,475 x 0,510 mm Typ
- B = 0,510 x 0,475 mm Typ
- C = 0,510 mm Sq Typ
- D = 0,575 x 0,540 mm Typ
- E = 0,510 x 0,540 mm Typ
- F = 0,640 x 0,540 mm
- G = 6,250 x 2,865 mm Typ
- H = 0,540 x 0,510 mm
- J = 0,575 x 0,510 mm
- K = 0,575 x 0,605 mm
- L = 0,575 x 0,540 mm

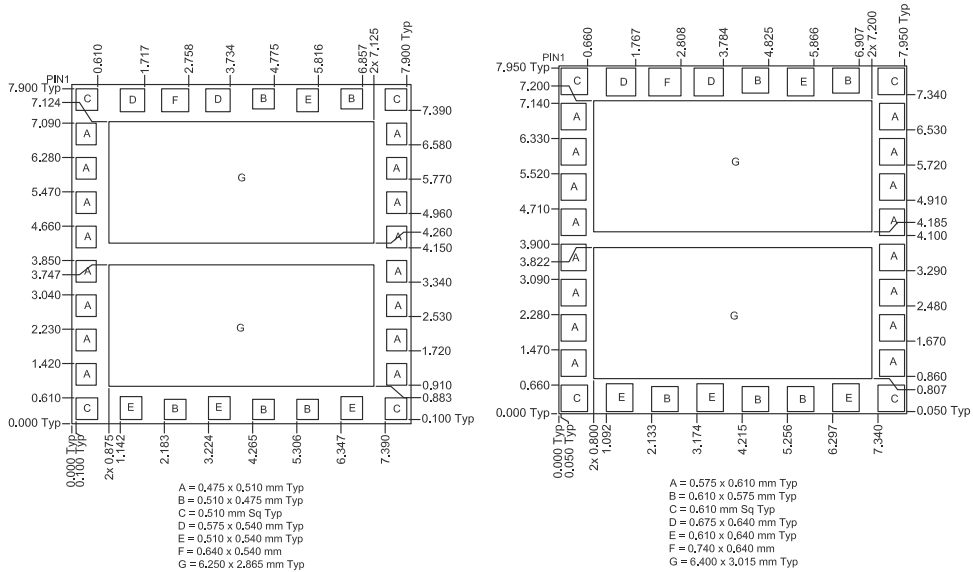
All units in μm .

Pin A = 510 x 475

Pin B = 510 x 510

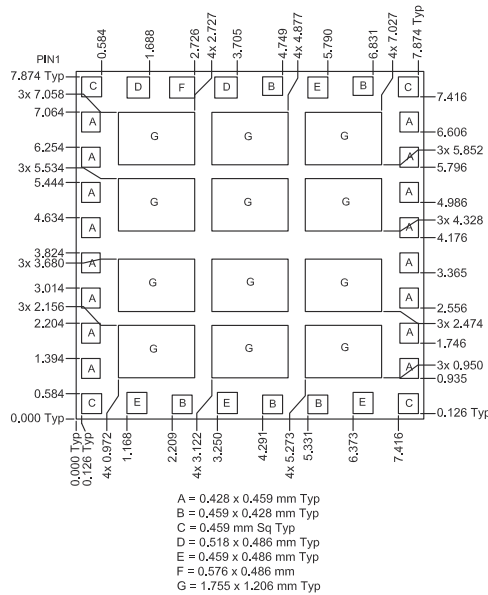
Pin C = 475 x 510

PCB Patterns



PCB MET/L LAND PATTERN

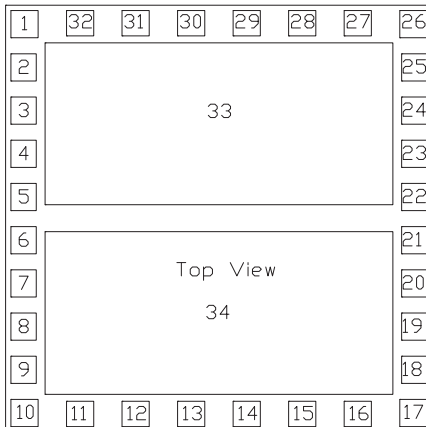
PCB SOLDER MASK PATTERN



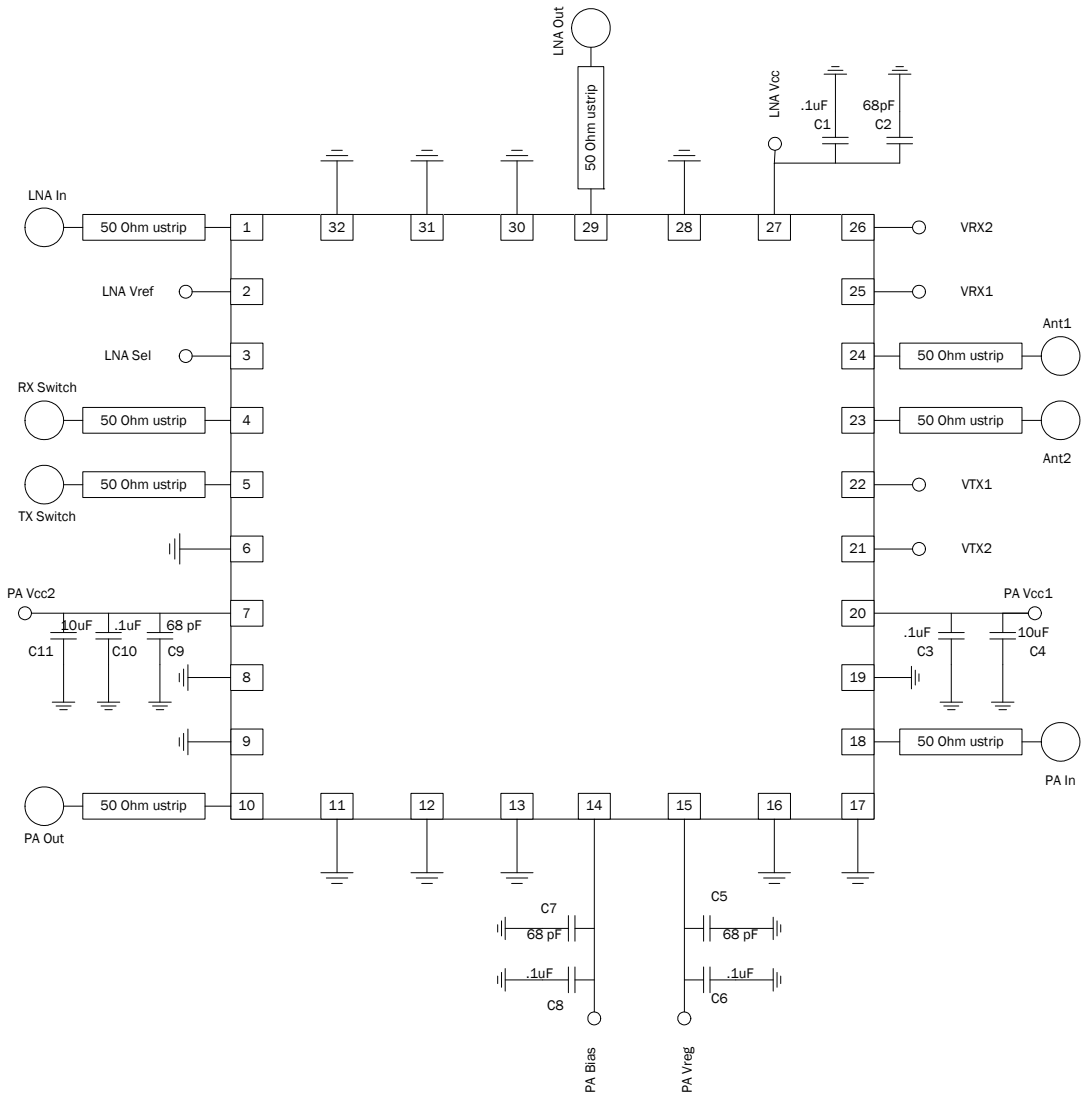
PCB STENCIL PATTERN

Thermal vias for center slug "G" should be incorporated into the PCB design. The number and size of thermal vias will depend on the application. Example of the number and size of vias can be found on the RFMD evaluation board layout.

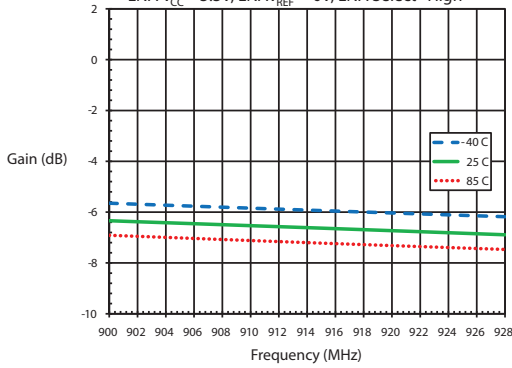
Pin Out



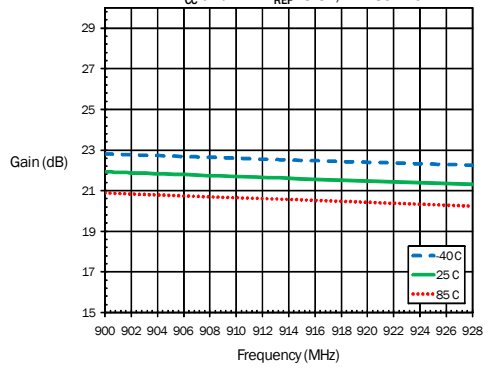
Application Schematic



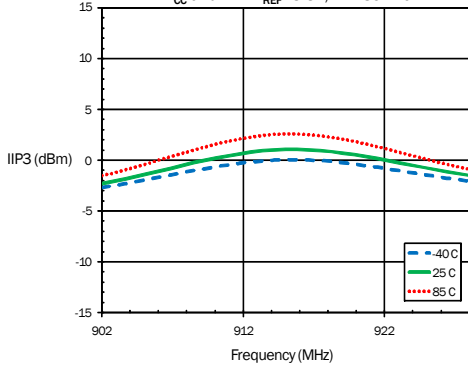
LNA Gain versus Frequency (Low Gain Mode)
Over Temperature
LNA $V_{CC} = 3.3V$, LNA $V_{REF} = 0V$, LNA Sel=High



LNA Gain versus Frequency (High Gain Mode)
Over Temperature
LNA V_{CC} and LNA $V_{REF} = 3.3V$; LNA Sel=Low



LNA IIP3 versus Frequency (In High Gain Mode)
(Over Temperature)
LNA V_{CC} and LNA $V_{REF} = 3.3V$; LNA Sel=Low



LNA IIP3 Vs Frequency (Low Gain Mode)
(Over Temperature)
LNA V_{CC} & LNA $V_{ref} = 3.3V$; LNA Sel = High

